



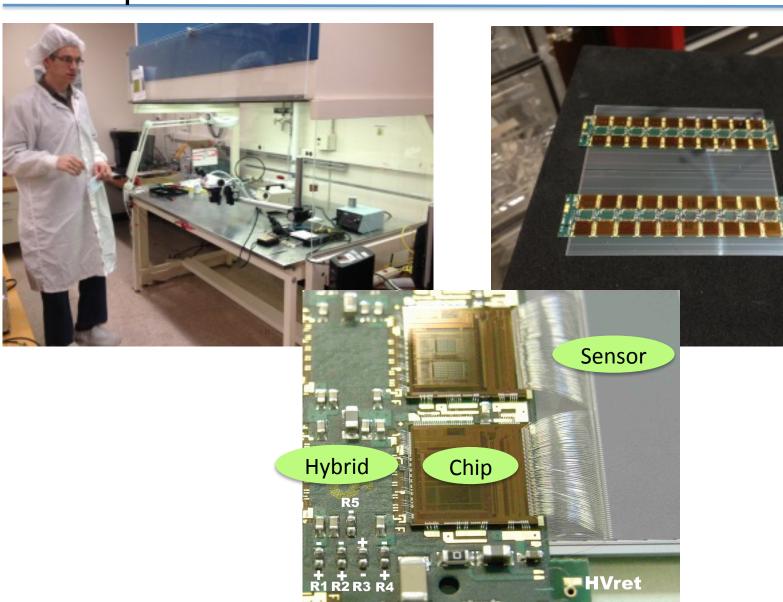
Silicon @ BNL Jessica Metcalfe

Outline



- Santa Cruz ITK strip production
- Santa Cruz HVCMOS studies
- U. Geneva HVCMOS studies
- Proposal for HVCMOS studies at BNL
- Lab Equipment





HVin



Production bench

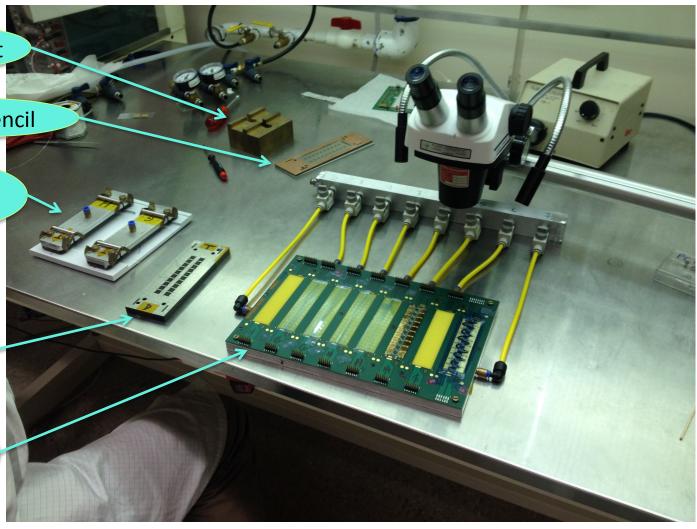
weight

Glue stencil

Vacuum grabber

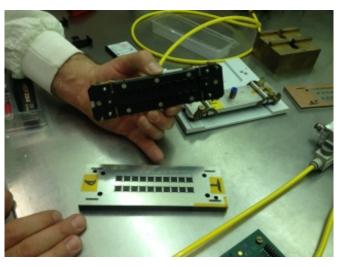
Jig: Chips

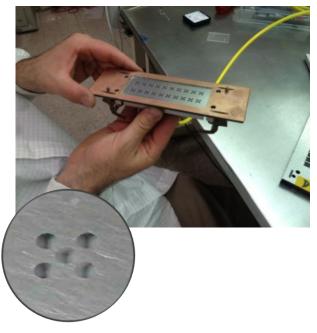
Hybrid frame







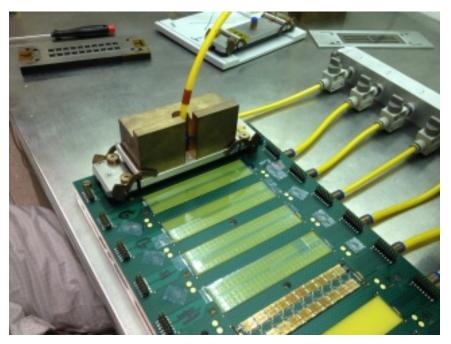




- 1) Prepare chips in jig for precision alignment
- 2) Vacuum tool to lift chips
- 3) Stencil for glue pattern on chips





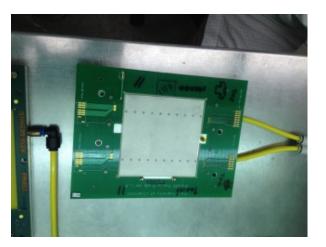


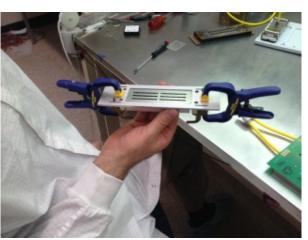
- 4) Apply glue
- 5) Align chips on hybrid and set glue
 -uniformity of glue thickness is very important

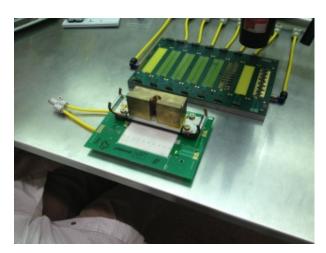
Chips are wire bonded and tested after the first gluing phase

A few wire bonds are used to connect to a test board and then later removed



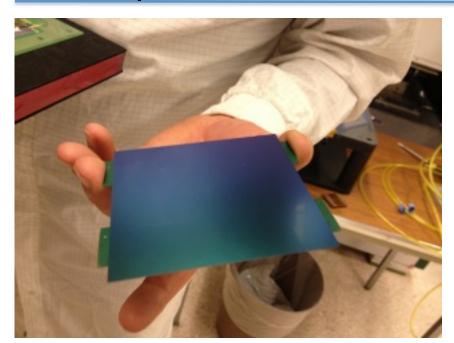


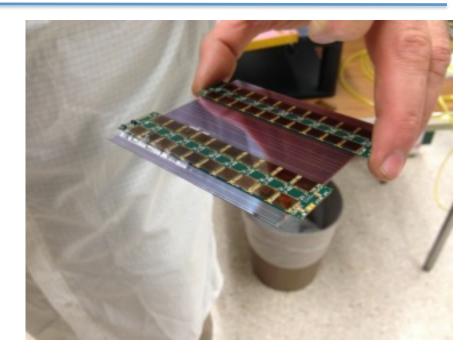




Gluing and testing process repeated for hybrid + sensor More tests are done after second gluing phase





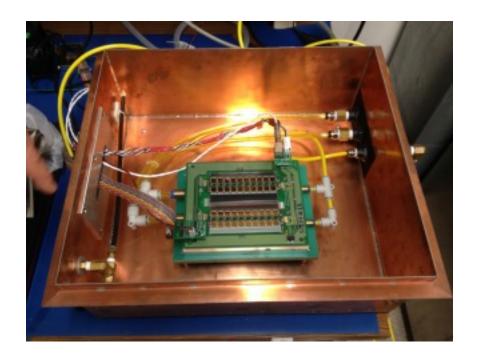


Finished Sensor module

ITK Strip Measurements



Production Module Test Station:



Light tight box
Cold vacuum chuck
Nitrogen flow
Electrical input/output connections

ITK Strip Measurements



Read-out for Strip Modules:



HCC controller with ABC130
High Speed IO board from SLAC
(upgrade to Atlys Digilent FPGA board)
Interlock (Cambridge)
SCT DAQ software -> automatic configuration, calibration tests, etc.

ITK Strip Measurements







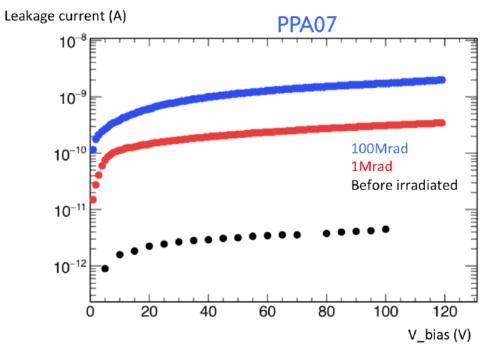
Visual inspection: Microscope Digital display

HVCMOS



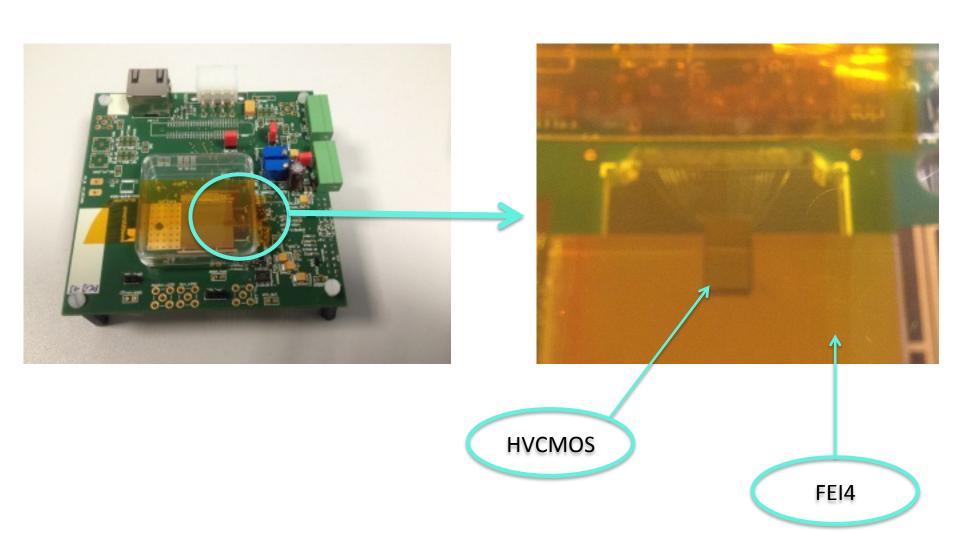
HVCMOS @ Santa Cruz

- Irradiation studies CHESS1
 - IV curves
 - Inter-strip resistance to study bias grid effects
 - Laser injection to study signal shape



Zhijun Liang (UCSC) https://indico.desy.de/ conferenceDisplay.py? confld=11834



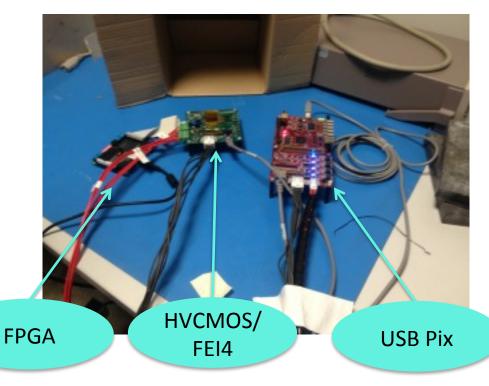


HVCMOS



University of Geneva @ CERN





Activities:

Threshold measurements: lowest ~500 electrons

Noise characterization

Testbeam

....more

HVCMOS

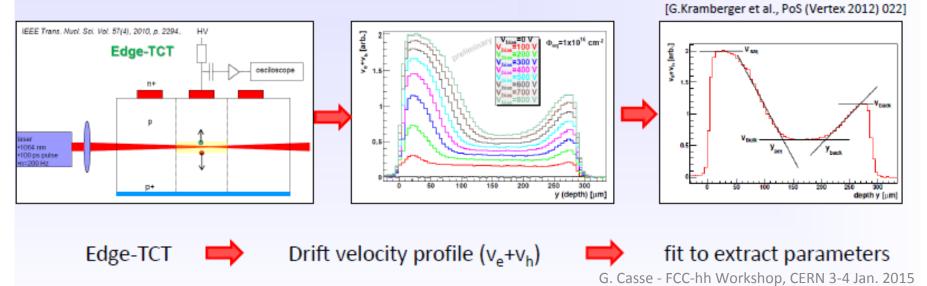


Proposed Activities for BNL:

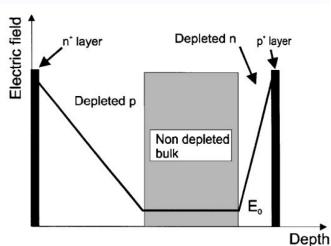
- Establish the lab
 - Basic setup, simple characterization
 - Reproduce some results from Geneva HVCMOS v2
- Transient current technique measurements
 - Pulse a laser on the sensor to induce signal
 - The effective doping concentration and electric field are inferred from the shape of the collected signal
 - Timing of the signal is highly dependent on E-field
 - High resistivity samples have a more uniform and stronger E-field
 - Resistivity is dependent on the doping concentration
 - U. Geneva et al. is planning to produce the next version of HVCMOS for 3 different resistivities in AMS-350
 - Ideal situation to compare E-field profile and timing
 - High E-field means you collect more charge quickly at drift velocities rather than via diffusion
- Source measurements would also be very welcome



- Parameterization of electric field instead?
 - Edge-TCT: Extract E-field (more precisely the drift velocity) profile and parameterize it



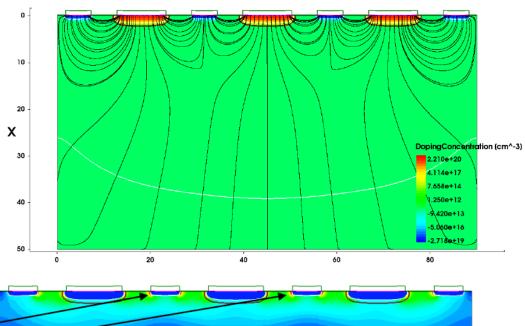
- Zheng Li developed TCT measurement technique at BNL
- Contacted Wei Chen—set up is still there
- May need a new laser to penetrate the HVCMOS

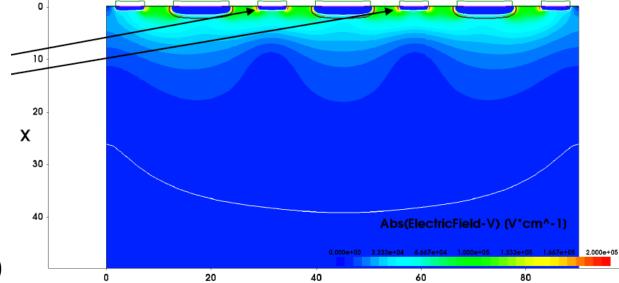




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Mathew Buckland (Liverpool)

https://indico.cern.ch/event/369680/

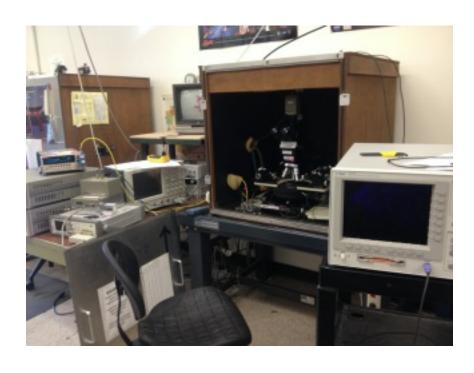
BNL Lab Equipment



Probe Station

- Light tight/electrically isolated/vibration damping
- Thermal vacuum chuck
- Nitrogen flow
- Chiller (at least -6° C, preferably -20° C)
- Pico probes (~5)
- Microscope
- Power supplies
- Oscilloscope
- Laser
- LCR meter
- Parameter Analyzer
- Computer

-much of this equipment should already exist in the lab



BNL Lab Equipment

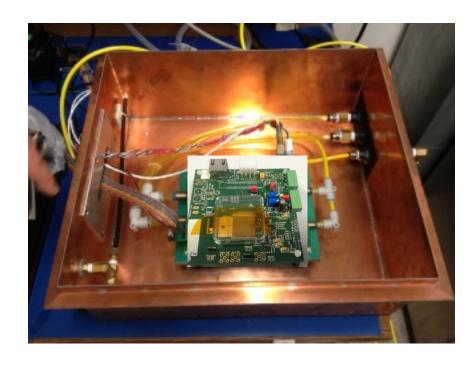


Test Bench

- Power supplies
- Oscilloscope
- Computer
- Device box—light tight, nitrogen flow, cooling

Misc. small equipment

- Cables, connectors, etc.
- Sources
- Freezer for storage after irradiation
- Thermal Chamber for annealing studies



BNL Lab Equipment



Desirable Equipment:

- Flip Chip machine for gluing/assembling small production scale -> fast turnover
- Infrared camera to debug heating/ power issues
- Smart Scope
 - XYZ programmable table
 - x5000 lens

